

BDT65; 65A
BDT65B; 65C

SILICON DARLINGTON POWER TRANSISTORS

NPN epitaxial base transistors in monolithic Darlington circuit for audio output stages and general purpose amplifier and switching applications. TO-220 plastic envelope. PNP complements are BDT64; BDT64A; BDT64B and BDT64C.

QUICK REFERENCE DATA

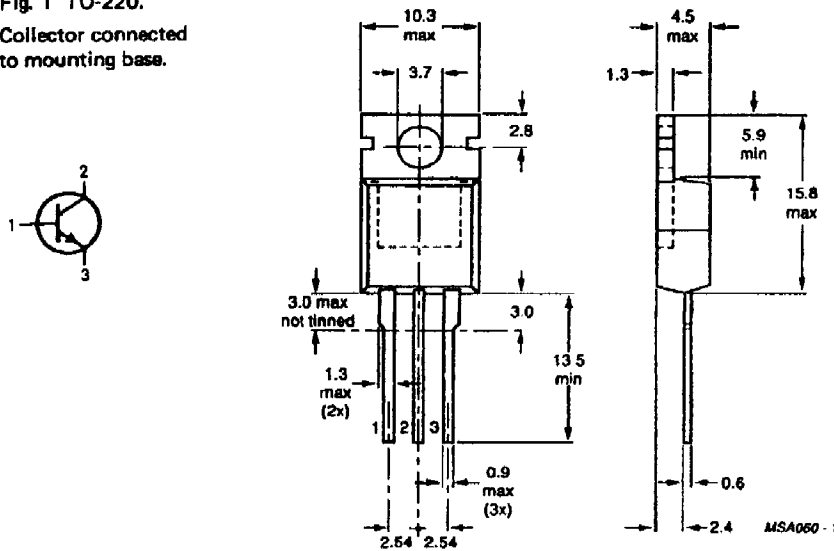
			BDT65	65A	65B	65C
Collector-base voltage (open emitter)	V_{CBO}	max.	60	80	100	120 V
Collector-emitter voltage (open base)	V_{CEO}	max.	60	80	100	120 V
Emitter-base voltage (open collector)	V_{EBO}	max.	5	5	5	5 V
Collector current (d.c.)	I_C	max.	12		A	
Total power dissipation up to $T_{mb} = 25^\circ\text{C}$	P_{tot}	max.	125		W	
Junction temperature	T_j	max.	150		$^\circ\text{C}$	
D.C. current gain $I_C = 5\text{ A}; V_{CE} = 4\text{ V}$	h_{FE}	>	1000			

MECHANICAL DATA

Dimensions in mm

Fig. 1 TO-220.

Collector connected to mounting base.



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